In the Claims:

- (original) A material comprising epitaxial Ba_xSr_{1-x}TiO₃ formed as a layer on the Cplane of a sapphire substrate, wherein x has a value from 0 to 1.
- (original) The material of Claim 1 wherein said layer is between about 100 and about 3000 nanometers thick.
- (original) The material of Claim 1 wherein said layer is between about 300 and about 1000 nanometers thick.
- 4. (original) The material of Claim 1 wherein said Ba_xSr_{1-x}TiO₃ has a 111 orientation.
- (original) The material of Claim 1 wherein said Ba_xSr_{1-x}TiO₃ is doped with an ion or ions that change its properties.
- (original) The material of Claim 5 wherein said doping ions comprise cesium and bismuth.
- (original) The material of claim 1 further comprising conductive electrodes for applying a bias or RF signal to the Ba_xSr_{1-x}TiO₃ layer.
- (original) A material comprising epitaxial Ba_xSr_{1-x}TiO₃ formed as a layer on a sapphire substrate, wherein x has a value from 0.1 to 0.9.
- 9. (original) The material according to Claim 8 wherein x has a value from 0.3 to 0.7.
- 10. (original) The material according to Claim 8 wherein x has a value from 0.4 to 0.6.
- 11. (original) The material of Claim 8 wherein said layer is between about 100 and about 3000 nanometers thick.
- 12. (original) The material of Claim 8 wherein said layer is between about 300 and about 1000 nanometers thick.
- 13. (original) The material of Claim 8 wherein said Ba_xSr_{1-x}TiO₃ has a 111 orientation.
- 14. (original) The material of Claim 8 wherein said Ba_xSr_{1-x}TiO₃ is doped with an ion or ions that change its properties.
- (original) The material of Claim 14 wherein said doping ions comprise cesium and bismuth.
- 16. (original) The material of Claim 8 further comprising conductive electrodes for applying a bias or RF signal to the Ba_xSr_{1-x}TiO₃ layer.